

BRC7002K2ZK

Rev.C May.-2022

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DATA SHEET

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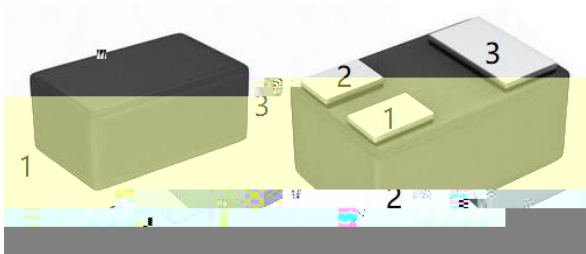
DFN1006-3L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a DFN1006-3L Plastic Package.

2KV

Sensitive gate trigger current and Low Holding current.ESD protected up to 2KV.HF Product.

Intended for use in general purpose switching and phase control applications.



Pin1:G

Pin2:S

Pin3:D

See Marking Instructions.

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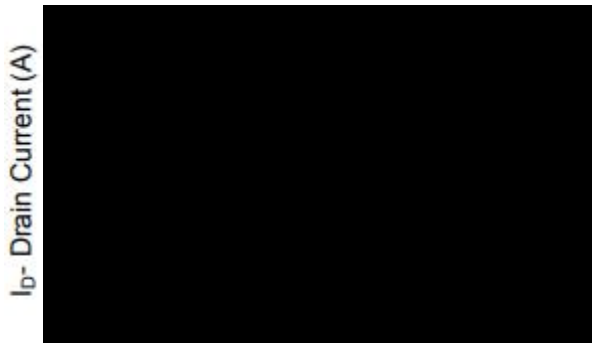
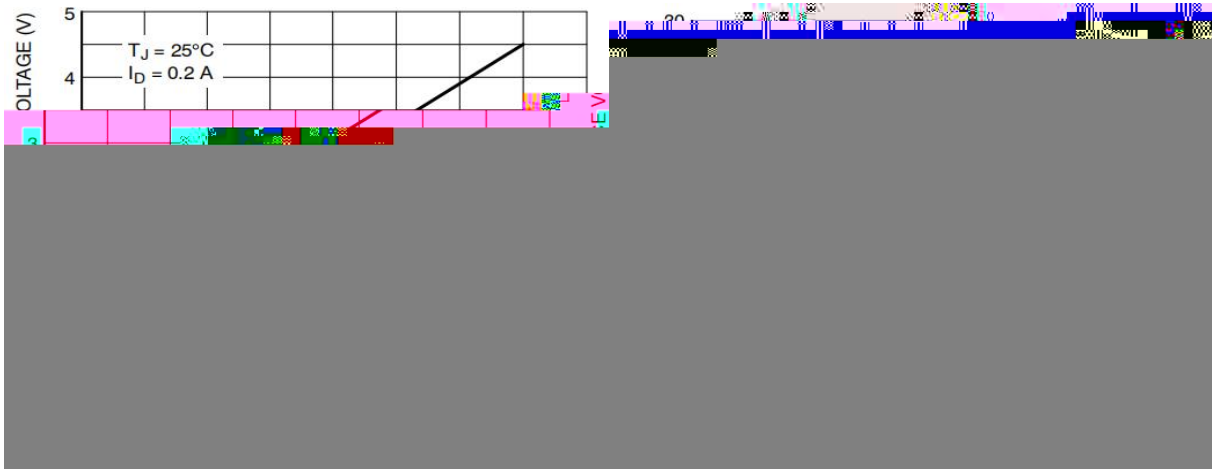
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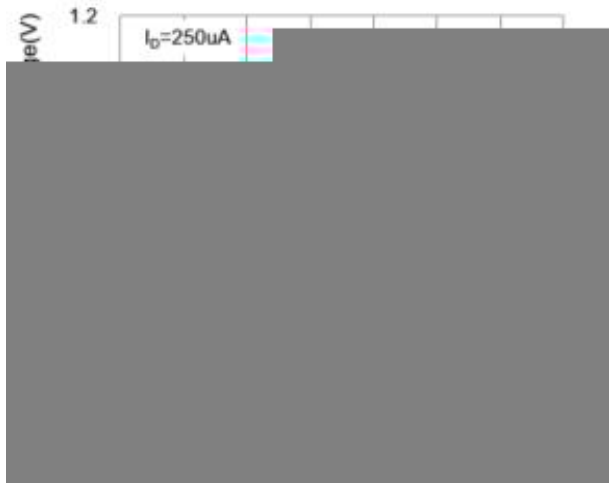
/ Electrical Characteristic Curve



I_D - Drain Current (A)

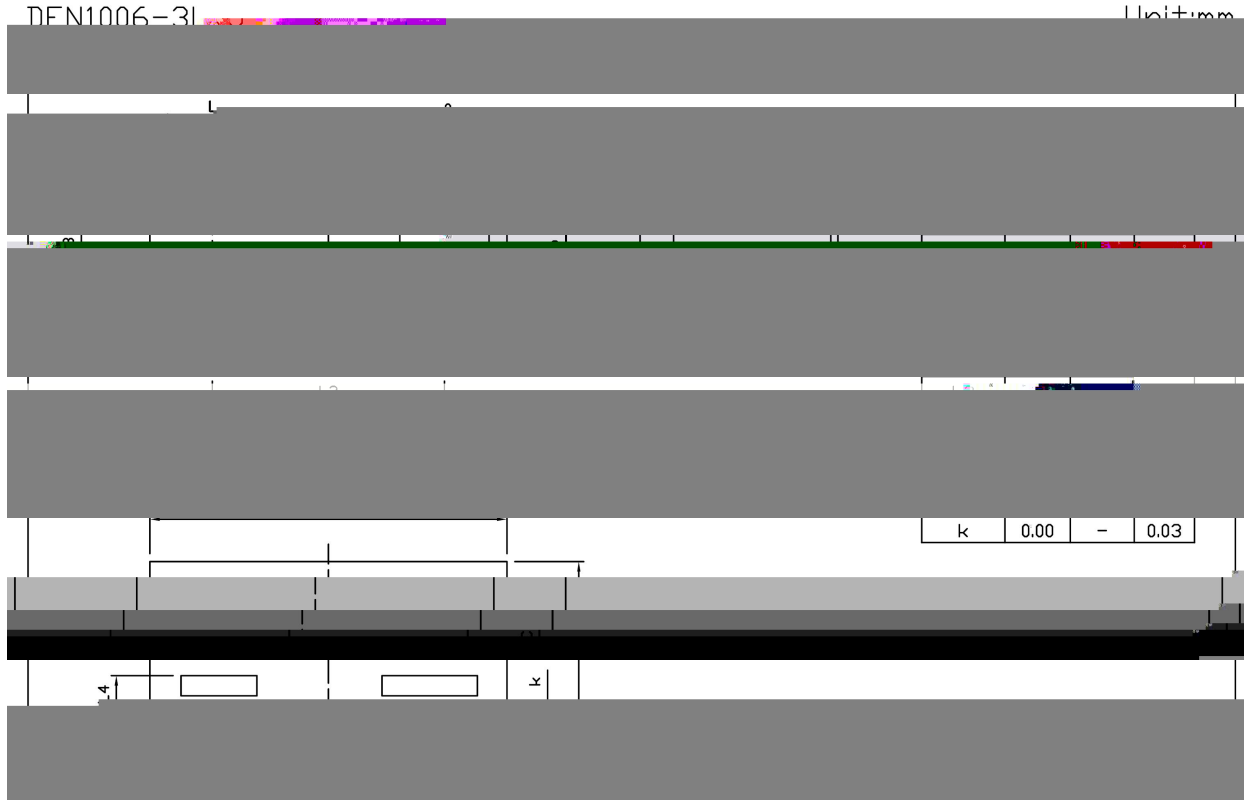
V_{ds} Drain-Source Voltage (V)

Figure 9 : Safe Operation Area





/ Package Dimensions



/ Marking Instructions



702K2

Note:

702K2: Product Type

